Gmail **Dr. Moumita Chakraborty <sumita.03@gmail.com>**

DECISION ON YOUR SUBMISSION ENTITLED “Investigation of the Electro-optical characteristics of Strain modulated SiNW based Exotic type IR pin photo-detector” WITH PAPER ID: 392

1 message

ICCECE 2026 <iccece2026@easychair.org> Wed, Jan 28, 2026 at 3:49 PM
To: Moumita Chakraborty <sumita03@gmail.com>

Dear authors,

Congratulations!

Your paper entitled, “Investigation of the Electro-optical characteristics of Strain modulated SiNW based Exotic type IR pin photo-detector” has been provisionally accepted for presentation in International Conference on Computer, Electrical & Communication Engineering (IEEE Conference ID # 69715). It will be formally accepted after at least you or any other co-author register as early as possible.

Please modify your paper if required based on the reviewer’s comments and prepare for power point presentation. Kindly complete the registration process by filling out the form accessible through the link: https://iccece.com/index1.php?id=7. Additionally, please send a copy of the camera-ready version of the paper, filled registration form (attached herewith), and scanned copy of paid bank challan with bank stamp to this email address registration@iccece.com with the subject line: Revised submission of paper for IEEE-ICCECE 2026 against conditional acceptance. Registration fees can be submitted through RTGS/NEFT also. In this case please attach the UTR number details along with your paper.

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PAPER ID: 392

TITLE: Investigation of the Electro-optical characteristics of Strain modulated SiNW based Exotic type IR pin photo-detector
REVIEWER’S OBSERVATION(S):

“The paper presents the design and analysis of a strain-engineered Silicon Nanowire (SiNW) based PIN infrared photodetector, operating in the 900–2300 nm IR wavelength range. The authors employ a self-consistent Quantum Modified Schrödinger–Poisson Drift–Diffusion (QMSP-DD) model, coupled with PSpice circuit simulation, to investigate electrical and electro-optical characteristics. A 3×4 array configuration is also proposed to enhance device performance. Simulation results are validated against experimental data, demonstrating improved photocurrent, responsivity, and quantum efficiency due to strain modulation.
Authors are go through the following comments:

1. The paper is simulation-heavy, with limited discussion on fabrication challenges of strain-modulated SiNW superlattices.
2. Noise performance metrics such as NEP and detectivity (D*) are not reported.
3. The discussion on Ge concentration optimization for strain induction could be expanded.”

Further please note: although the paper has been ACCEPTED for presentation at the IEEE-ICCECE 2026 International Conference, your paper would further be scrutinized by the IEEE peer-review system prior to acceptance for the IEEE-Xplore digital library platform and may require further time for final acceptance by IEEE-Xplore digital library.

Expecting to see you in our conference.

Regards
Prof. Bidyut Baran Chaudhuri
Editor
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